

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1191	(438/592).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 09:26
L3	913	438/592.ccls. and @ad<="20011004"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:18
L4	11132	semiconductor and (polysilicon with (stop\$6 or barrier or (silicon adj nitride))) and @ad<="20011004"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:20
L5	6932	semiconductor and (polysilicon with (silicon adj nitride)) and @ad<="20011004"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:47
L6	2	semiconductor and (polysilicon with ((silicon adj nitride) adj within)) and @ad<="20011004"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:22
L7	8	semiconductor and (polysilicon with ((stop\$6 or (silicon adj nitride)) adj within)) and @ad<="20011004"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:23
L8	757	L5 and (polysilicon same (("within") or ("in") or ("inside")) same (stop\$6 or (silicon adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:51
L9	69	L3 and (polysilicon same (("within") or ("in") or ("inside")) same (stop\$6 or (silicon adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 10:51

L10	1186	(438/585).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 13:23
L11	209	(438/588).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 13:23
L12	1191	(438/592).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 13:23
L13	786	(438/595).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 13:23
L15	2013	(438/257).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 13:23
L16	2092	(438/656).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 13:23
L17	765	(438/648).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 13:24
L18	475	(438/649).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 13:24

L19	12450	(gates and semiconductor) and (etch\$3 adj stop\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:25
L20	6125	((gates and semiconductor) and (etch\$3 adj stop\$4)) and (sidewalls)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:25
L21	4822	(gates and semiconductor) and (etch\$3 adj stop\$4) and ("438" and "257")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:26
L22	1027	438/585,588,592,595,257,656, 648,649.ccls. and (etch\$3 adj stop\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:26
L23	1481	438/585,588,592,595,257,656, 648,649.ccls. and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:28
L24	0	(438/585,588,592,595,257,656, 648,649.ccls. same ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:28
L25	0	(438/585,588,592,595,257,656, 648,649.ccls. same ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:28
L26	1008	438/585,588,592,595,257,656, 648,649.ccls. and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:29
L27	1008	438/585,588,592,595,257,656, 648,649.ccls. and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:29

L28	2	438/585,588,592,595,257,656, 648,649.ccls. and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004" and (((poly-metal) or (poly adj metal) or (polysilicon adj metal)) adj stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:29
L29	81	438/585,588,592,595,257,656, 648,649.ccls. and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004" and (((poly-metal) or (poly adj metal) or (polysilicon adj metal)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 13:30
S71	16	((("20030074176") or ("20020052883") or ("20020062206") or ("20020188911") or ("20030005393") or ("20030109995") or ("20020052883") or ("20020062206") or ("20020188911") or ("20030005393") or ("20030109995") or ("20020094657") or ("20040021161") or ("20020009823") or ("6380579") or ("6570186") or ("6699777") or ("6001540") or ("5976908") or ("6137127") or ("6245650")).PN.	US-PGPUB; USPAT	OR	OFF	2005/03/14 10:10
S72	60	438/585,588,592,595,257,656, 648,649.ccls. and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and (oxidat\$3 or oxidiz\$6) and @ad<="20011004" and (((poly-metal) or (poly adj metal) or (polysilicon adj metal)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:08
S73	81	438/585,588,592,595,257,656, 648,649.ccls. and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004" and (((poly-metal) or (poly adj metal) or (polysilicon adj metal)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:09
S74	1007	438/585,588,592,595,257,656, 648,649.ccls. and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:11

S75	16	438/585,588,592,595,257,656, 648,649.ccls. and (poly-metal) and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:23
S76	35	"438"/\$.ccls. and (poly-metal) and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:13
S77	43	"257"/\$.ccls. and (poly-metal) and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:13
S78	53	semiconductor and (poly-metal) and ((etch\$3 or remov\$4 or polish\$4) adj (stop\$4 or ((silicon adj nitride) or (SiN)))) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:13
S79	34	438/585,588,592,595,257,656, 648,649.ccls. and (poly-metal) and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:23
S80	5827	438/585,588,592,595,257,656, 648,649.ccls. and @ad<="20011004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/14 09:24